Planar waveguide devices on an Si-compatible technology platform

University of Twente, Lightwave Devices Group, MESA+ Research Institute
P.O.Box 217, 7500AE Enschede, The Netherlands

Research and development in the field of integrated optics devices for communication application and sensing purposes has been extremely speeded up over the last decade [1]. The main motivation beyond this development arises from the rapidly increased need of today’s information society for fast data transfer. In principle, the integrated optics devices can be realized in various materials systems and technologies, e.g. LiNbO$_3$, doped silica, III-V materials, polymers, silicon oxynitride, etc. For each of them advantages and drawbacks can be pointed out. For the majority of our integrated optics devices, an Si-compatible technology platform is applied. Mostly, a silicon oxynitride (SiON) waveguide forms the basic building block [2]. This material is highly attractive for integrated optics due to the following properties:

- Large refractive index range (1.45 for SiO$_2$ up to 2.01 for Si$_3$N$_4$ or 3.5 for silicon) allowing for low- and high contrast application
- Low optical loss (< 0.2 dB/cm for visible light, for 3$^\text{rd}$ telecommunication window losses increased due to N-H and Si-H overtones, however losses are decreased to below 0.2 dB/cm by annealing, Fig. 1)
- High uniformity, homogeneity and reproducibility of layer thickness (within 1%) and refractive index (better than 0.05%)
- Access to reliable technology (PECVD, LPCVD, RIE, etc.) for fabrication of various waveguiding structures, Fig. 2 and 3

The major drawback of silicon-based technology is given by the lack of active functionality. Nevertheless, this drawback can be overcome when combining the SiON-based waveguide platform with materials yielding special properties. In recent research, this hybrid approach has been successfully applied, e.g.:

- Er doped Al$_2$O$_3$ and Y$_2$O$_3$ [3], allowing for light generation in the 3$^\text{rd}$ telecommunication window
- Polymers [4], exploiting the high thermo-optic coefficient of this material
- ZnO [5], implementing electro-optic activity at desired positions of the integrated optics circuit

References